

Appl. No. 09/817,963
Amdt. dated 4/26/06
Reply to Office action of 11/28/05

CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-3 (previously canceled).

Claim 4 (currently amended). A process for metallizing at least one insulating layer of an electronic or microelectronic component, which comprises:

applying at least one first insulating layer to a substrate such that the first insulating layer has a thickness not greater than ~~50~~ 50 μm;

activating the entire first insulating layer by treatment with an activator, the activator being at least one of a gas, a liquid, a solution, and a plasma;

then, after activating the entire first insulating layer, applying to the first insulating layer a second insulating layer made of a photosensitive material, and patterning a second the second insulating layer made of a photosensitive material; and

Appl. No. 09/817,963
Amdt. dated 4/26/06
Reply to Office action of 11/28/05

then, after applying and patterning the second insulating layer, seeding and metallizing regions of the first insulating layer that are exposed by the patterning step.

Claim 5 (previously presented). The process according to claim 4, which comprises forming the first insulating layer and the second insulating layer from the same material.

Claim 6 (previously presented). The process according to claim 5, which comprises patterning the first insulating layer before the entire first layer is activated and before the second insulating layer is applied.

Claim 7 (previously presented). The process according to claim 4, which comprises patterning the first insulating layer before the entire first layer is activated and before the second insulating layer is applied.

Claim 8 (new). The process according to claim 4, wherein the first insulating layer is a buffer coating.